EMF18XV6T5

Dual Transistor - Power Management

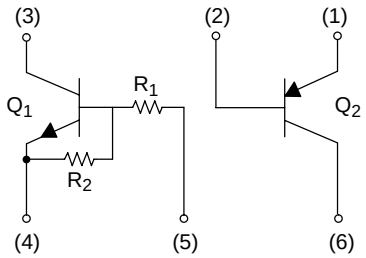
NPN/PNP Dual (Complimentary)

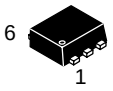
ON Semiconductor®

http://onsemi.com

Features

- Low $V_{CE(SAT)}$, < 0.5 V
- These are Pb−Free Devices





SOT−563
CASE 463A
PLASTIC

MAXIMUM RATINGS

Q1

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

Q2

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	−60	V
Collector−Base Voltage	V_{CBO}	−50	V
Emitter−Base Voltage	V_{EBO}	−6.0	V
Collector Current − Continuous	I_C	−100	mAdc

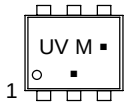
THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D	357 (Note 1) 2.9 (Note 1)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 1)	°C/W
Characteristic (Both Junctions Heated)	**Symbol**	**Max**	**Unit**
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D	500 (Note1) 4.0 (Note 1)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	250 (Note 1)	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR−4 @ Minimum Pad.

MARKING DIAGRAM



UV = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
EMF18XV6T5	SOT−563 (Pb−Free)	8000/Tape & Reel
EMF18XV6T5G	SOT−563 (Pb−Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications

ELECTRICAL CHARACTERISTICS (T_A = 25°C) (Note 2)

Characteristic	Symbol	Min	Typ	Max	Unit
Q1: NPN					
Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)	I_{CBO}	−	−	100	nAdc
Collector-Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)	I_{CEO}	−	−	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	I_{EBO}	−	−	0.1	mAdc
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$	50	−	−	Vdc
Collector-Emitter Breakdown Voltage (Note 4) (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	50	−	−	Vdc
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	h_{FE}	80	140	−	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA)	$V_{CE(sat)}$	−	−	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 3.5 V, R_L = 1.0 kΩ)	V_{OL}	−	−	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ)	V_{OH}	4.9	−	−	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ
Resistor Ratio	R1/R2	0.8	1.0	1.2	
Q2: PNP					
Collector−Base Breakdown Voltage (I_C = −50 μAdc, I_E = 0)	$V_{(BR)CBO}$	−60	−	−	Vdc
Collector−Emitter Breakdown Voltage (I_C = −1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	−50	−	−	Vdc
Emitter−Base Breakdown Voltage (I_E = −50 μAdc, I_E = 0)	$V_{(BR)EBO}$	−6.0	−	−	Vdc
Collector−Base Cutoff Current (V_{CB} = −30 Vdc, I_E = 0)	I_{CBO}	−	−	−0.5	nA
Emitter−Base Cutoff Current (V_{EB} = −5.0 Vdc, I_B = 0)	I_{EBO}	−	−	−0.5	μA
Collector−Emitter Saturation Voltage (Note 4) (I_C = −50 mAdc, I_B = −5.0 mAdc)	$V_{CE(sat)}$	−	−	−0.5	Vdc
DC Current Gain (Note 4) (V_{CE} = −6.0 Vdc, I_C = −1.0 mAdc)	h_{FE}	120	−	560	−
Transition Frequency (V_{CE} = −12 Vdc, I_C = −2.0 mAdc, f = 30 MHz)	f_T	−	140	−	MHz
Output Capacitance (V_{CB} = −12 Vdc, I_E = 0 Adc, f = 1.0 MHz)	C_{OB}	−	3.5	−	pF

3. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.
4. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

TYPICAL ELECTRICAL CHARACTERISTICS — Q1, NPN

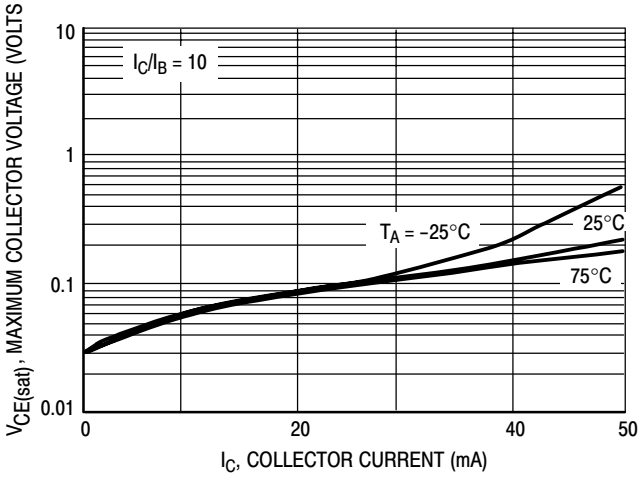


Figure 1. $V_{CE(sat)}$ versus I_C

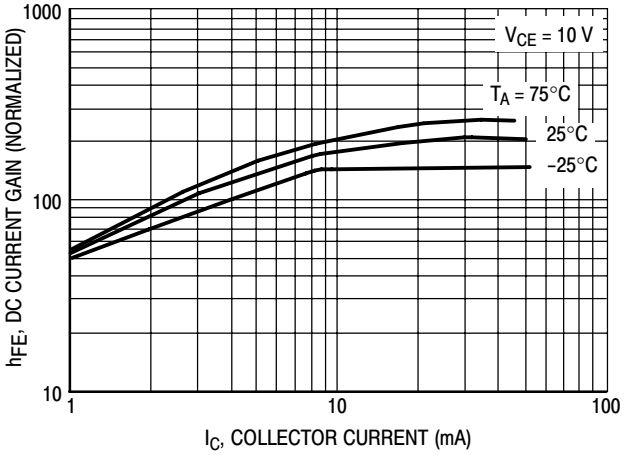


Figure 2. DC Current Gain

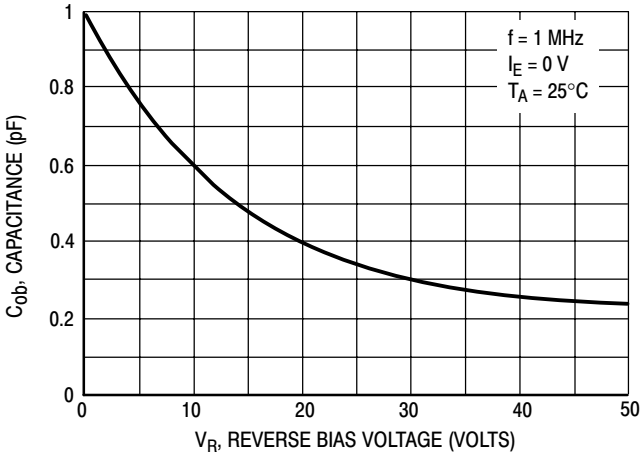


Figure 3. Output Capacitance

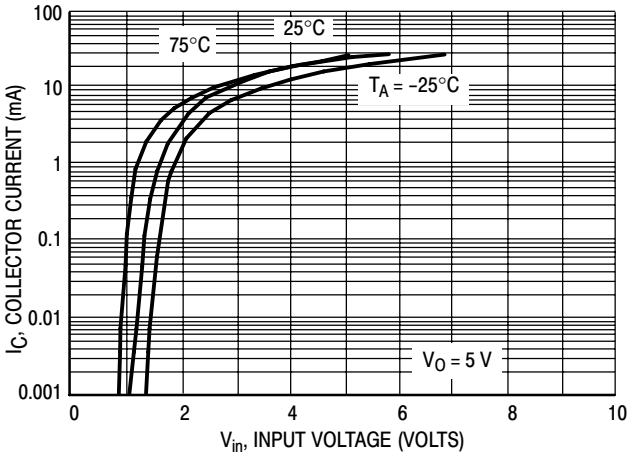


Figure 4. Output Current versus Input Voltage

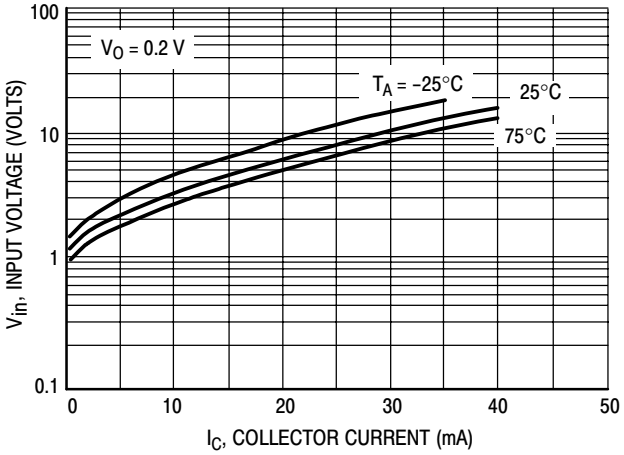


Figure 5. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS − Q2, PNP

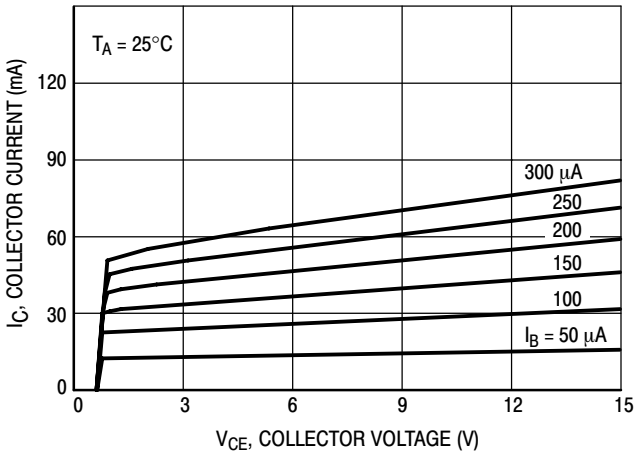


Figure 6. I_C − V_{CE}

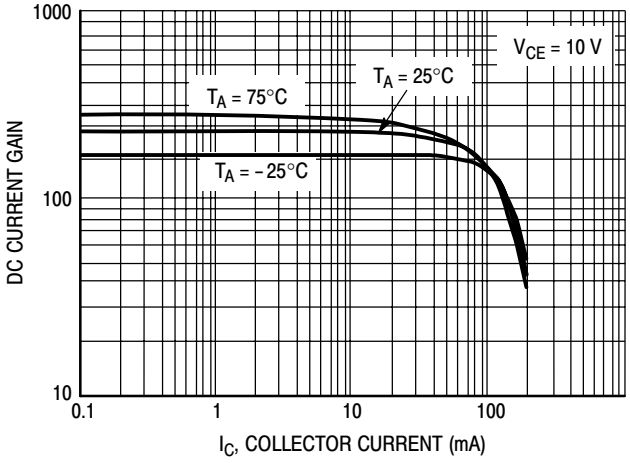


Figure 7. DC Current Gain

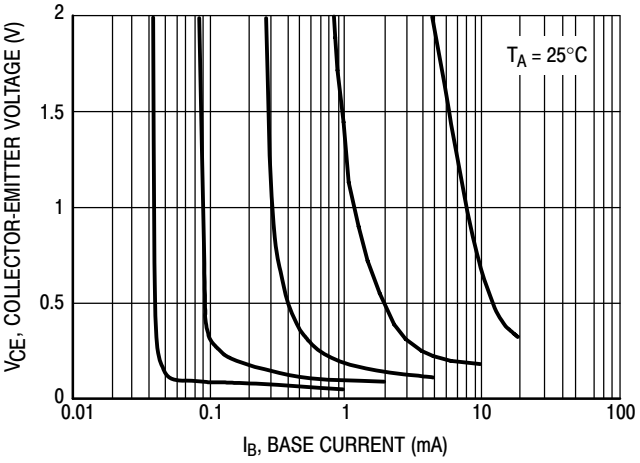


Figure 8. Collector Saturation Region

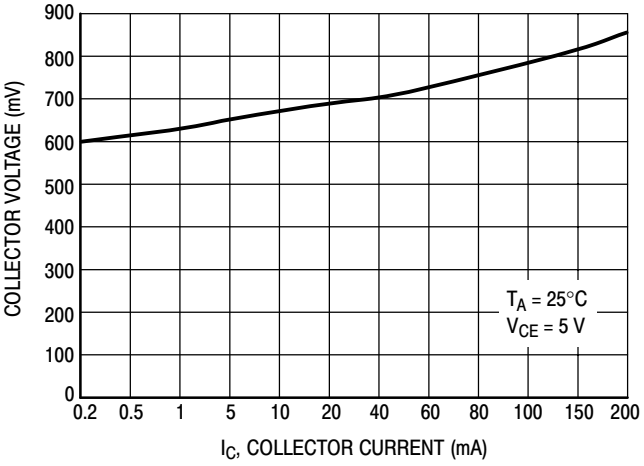


Figure 9. On Voltage

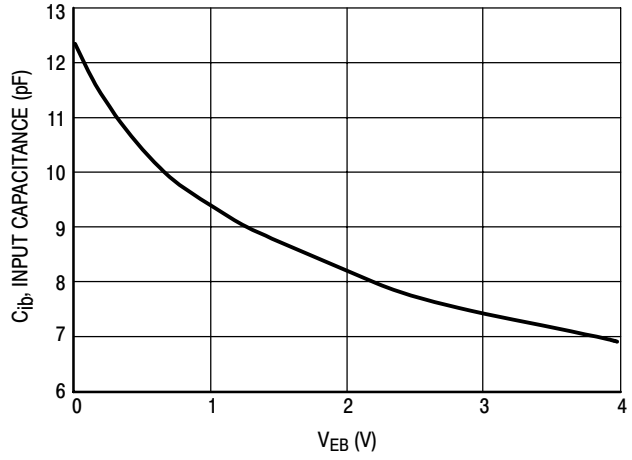


Figure 10. Capacitance

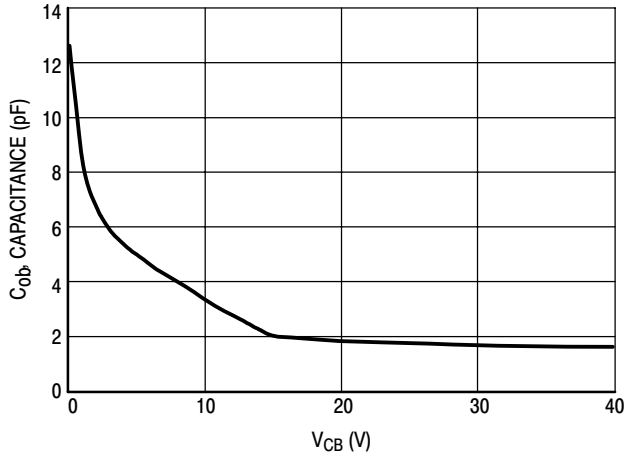
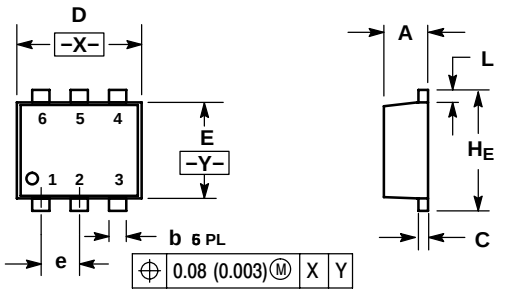


Figure 11. Capacitance

EMF18XV6T5

PACKAGE DIMENSIONS

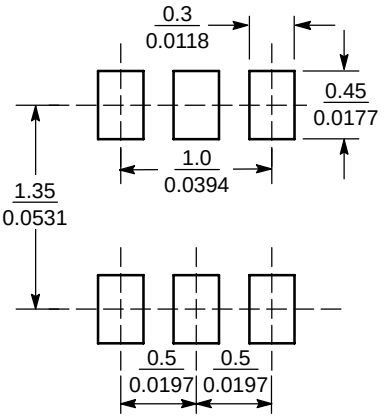
SOT−563, 6 LEAD
CASE 463A−01
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	1.50	1.60	1.70	0.059	0.062	0.066

SOLDERING FOOTPRINT*



SCALE 20:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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